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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: SHIH et al.  
Application No.: 10/666,331  
Filed: 9/17/2003

Examiner: KORNAKOV, Michail  
Group No.: 1746  
Confirmation No.: 8374

Title: METHODS FOR CLEANING A SET OF  
STRUCTURES COMPRISING YTTRIUM OXIDE IN  
A PLASMA PROCESSING SYSTEM

INFORMATION DISCLOSURE STATEMENT

## OTHER DOCUMENTS

Examiner Initials	Cite No.	Description	T
MK	1	GEORGE, H. Bola, "In-Situ Analysis of High Density Plasma Enhanced Chemical Vapor Deposition of Thin Films," October 13, 1999, 17 slides total	
MK	2	"Acetone," <a href="http://www.wikipedia.org/wiki/Acetone">http://www.wikipedia.org/wiki/Acetone</a> , 2 pages total	
MK	3	JOHNSON et al., "Reducing PFC gas emissions from CVD chamber cleaning," Solid State Technology, December 2000, 6 pages total	
MK	4	"Hydrogen Peroxide (H <sub>2</sub> O <sub>2</sub> ): the Amazing Secrets That THEY Don't Want You to Know!," <a href="http://www.h2o2-4u.com/">http://www.h2o2-4u.com/</a> , 6 pages total	
MK	5	HORIUCHI et al., "In-Situ Chamber Wall Cleaning in Processing Plasmas," 4 pages total	
MK	6	FRIZ et al., "Coating Materials," pp. 105-130	
MK	7	YEOH et al., "Photoresist Strip on Orion2.2™ in-Via First Dual Damascene Cu Structures," Trikon Technologies, 3 pages total	
MK	8	"Yttrium Oxide Products: Ideal for Titanium Processing," ZYP Coatings Inc., 8 pages total	
MK	9	NELSON et al., "Yttrium Oxide Nanoparticles Prepared by Alkalide Reduction," Chem. Mater. 2002, 14, pp. 915-917	
MK	10	"Chemical of the Week: Ammonia, NH <sub>3</sub> ," <a href="http://scifun.chem.wisc.edu/chemweek/ammonia/ammonia.html">http://scifun.chem.wisc.edu/chemweek/ammonia/ammonia.html</a> , 3 pages total	
MK	11	"I. Introduction," BE 4283/6283 SiC RIE lab project, MS State University, 6 pages total	
MK	12	"Thermal Spray Coatings: Nature of Thermal Spray Coatings," 10 pages total, <a href="http://www.gordonengland.co.uk/tsc.htm">http://www.gordonengland.co.uk/tsc.htm</a>	
MK	13	NICKERSON et al., "Plasma Cleaning of Medical Devices," Critical Cleaning in Precision Manufacturing, 4 pages total	
MK	14	SOBOLEWSKI et al., "Electrical Optimization of Plasma-enhanced Chemical Vapor Deposition Chamber Cleaning Plasmas," J. Vac. Sci. Technol. B 16(1), Jan/Feb 1998, pp. 173 - 182	
MK	15	"Plasma Spray Process," <a href="http://www.gordonengland.co.uk/ps.htm">http://www.gordonengland.co.uk/ps.htm</a> , 3 pages total	

Examiner Signature	<i>mkj</i>	Date Considered	03/03/07
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<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  <u>(Use Several Sheets if Necessary)</u>	<b>Atty Docket No.</b> LMRX-P023/P1130  <b>Applicant:</b> SHIH et al.  <b>Filing Date</b> 9/17/2003	<b>Application No.:</b> 10/666,331  <b>Group</b> 1746
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## **U.S. Patent Documents & Published Applications**

**Foreign Patent or Published Foreign Patent Application**

## **Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	4	PCT International Search Report mailed 19 MAY 2005, PCT/US04/30430
	5	Written Opinion of ISR, PCT/US04/30430
Examiner	Date Considered	

**Examiner:** Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<b>Form 1449 (Modified)</b>	Atty Docket No. LMRX-P023/P1130	Application No.: 10/666,331
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(Use Several Sheets if Necessary)	Filing Date 9/17/2003	Group 1746

## **U.S. Patent Documents & Published Applications**

**Foreign Patent or Published Foreign Patent Application**

## **Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	I	IPRP (International Preliminary Report on Patentability) mailed 30 MAR 2006, PCI/US2004/030430
Examiner		Date Considered
		03/03/07

**Examiner:** Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.